

Docket: CS 99 - 065

S/N: 09/442,499

To: Commissioner of Patents and Trademarks
Washington, D.C. 20231

From: George O. Saile, Reg. No. 19,572
20 McIntosh Drive
Poughkeepsie, N.Y. 12603

Subject:

Divisional Application Based upon Parent Application Serial
No.: 09/442,499, Filed: 11/18/99

Serial No. TBD

Inventor: Ho

Title: Plasma Etch Method For Forming Plasma Etched Silicon
Layer

Group Art Unit: 1763

Examiner: Goudreau, G. A.

Attorney Docket: CS 99 - 065B

PRELIMINARY AMENDMENT

Dear Sir:

In conjunction with the Divisional Application filed herewith,
please consider the following remarks:

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the
United States Postal Service as first class mail in an envelope addressed to:

Commissioner for Patents, P.O. Box 1450, Alexandria, Virginia 22313-1450, on ____

October 27, 2003.

Signature/Date  10/27/03

Stephen B. Ackerman

Reg. No. 37,761

October 27, 2003

To: Commissioner of Patents and Trademarks
Washington, D.C. 20231

Fr: George O. Saile Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject:

Divisional Patent Application of
Serial No.: 09/442,499 11/18/99

PAUL KWOK KEUNG HO, XUE CHUN DAI

PLASMA ETCH METHOD FOR FORMING PLASMA
ETCHED SILICON LAYER

PRELIMINARY AMENDMENT

Dear Sir:


This is a preliminary amendment for the above referenced Divisional Patent
Application. Please amend the above identified application for patent as follows:

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States
Postal Service as first class mail in an envelope addressed to: Commissioner of Patents
and Trademarks, Washington, D.C. 20231, on October 27, 2003.

Stephen B. Ackerman, Reg. No. 37,761

Signature/Date

 10/27/03